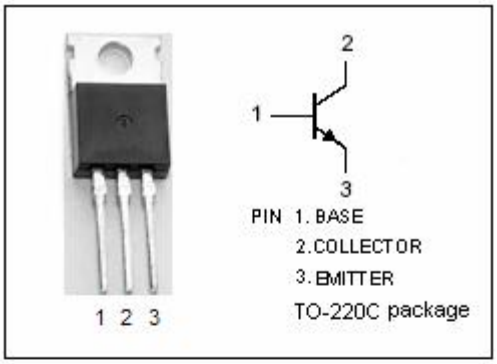
isc Silicon NPN Power Transistor BDX75



DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 40V (Min)
- High Current Capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

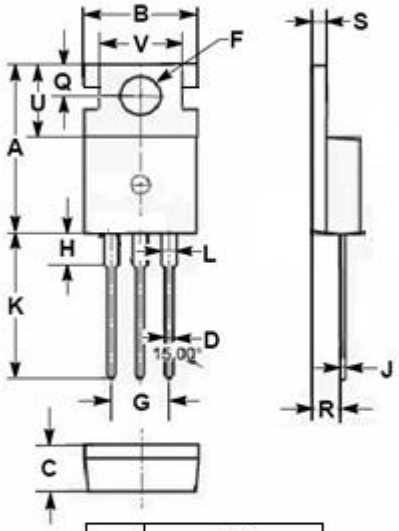
- Designed for use in general-purpose amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	45	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	16	A
P_C	Collector Power Dissipation @ T_C=25℃	75	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.67	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	70	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	40		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 16A; I_B= 3.2A		2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 8A ; V_{CE}= 4V		1.7	V
I_{CEX}	Collector Cutoff Current	V_{CE}= 45V; V_{BE}= -1.5V V_{CE}= 45V; V_{BE}= -1.5V;T_C=150℃		2.0 10	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 40V; I_B= 0		2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C= 0		1.0	mA
h_{FE-1}	DC Current Gain	I_C= 8A ; V_{CE}= 4V	15	60	
h_{FE-2}	DC Current Gain	I_C= 16A ; V_{CE}= 4V	5		
f_T	Current-Gain—Bandwidth Product	I_C= 1A ; V_{CE}= 4V, f_{test}= 0.1MHz	3		MHz